

## Outline

- Content-Addressable Memories
$\square$ Read-Only Memories
$\square$ Programmable Logic Arrays


## CAMs

- Extension of ordinary memory (e.g. SRAM)
- Read and write memory as usual
- Also match to see which words contain a key



## 10T CAM Cell

- Add four match transistors to 6T SRAM
$-56 \times 43 \lambda$ unit cell




## CAM Cell Operation

$\square$ Read and write like ordinary SRAM
$\square$ For matching:

- Leave wordline Iow
- Precharge matchlines
- Place key on bitlines
- Matchlines evaluate
$\square$ Miss line

- Pseudo-nMOS NOR of match lines
- Goes high if no words match


## Read-Only Memories

$\square$ Read-Only Memories are nonvolatile

- Retain their contents when power is removed
$\square$ Mask-programmed ROMs use one transistor per bit
- Presence or absence determines 1 or 0


## ROM Example

- 4-word x 6-bit ROM
- Represented with dot diagram Word 1: 011001
- Dots indicate 1's in ROM


Word 0: 010101

Word 2: 100101
Word 3: 101010


Looks like 6 4-input pseudo-nMOS NORs

## ROM Array Layout

U Unit cell is $12 \times 8 \lambda$ (about $1 / 10$ size of SRAM)


## Row Decoders

$\square$ ROM row decoders must pitch-match with ROM

- Only a single track per word!



## Complete ROM Layout



## PROMs and EPROMs

- Programmable ROMs
- Build array with transistors at every site
- Burn out fuses to disable unwanted transistors
$\square$ Electrically Programmable ROMs
- Use floating gate to turn off unwanted transistors
- EPROM, EEPROM, Flash



## Flash Programming

Charge on floating gate determines $V_{t}$

- Logic 1: negative $\mathrm{V}_{\mathrm{t}}$
- Logic 0 : positive $V_{t}$
- Cells erased to 1 by applying a high body voltage so that electrons tunnel off floating gate into substrate
$\square$ Programmed to 0 by applying high gate voltage

| 0 V | 20 V | 20 V | 20 V | 10 V |
| :---: | :---: | :---: | :---: | :---: |
| $\perp$ | $\perp$ | $\perp$ | $\perp$ | $\perp$ |
| L | $\sqrt{\text { ¢ }}$ | 0 V | 8 V ل 8 V | ? ${ }^{\text {? }}$ |
| 20 V | 20 V | 0 V | 0 V | 0 V |
|  | Inhibit |  | Do Not | Inhibit |
| Erase | Erase | Program 0 | Program | Program |

## NAND Flash

$\square$ High density, low cost / bit

- Programmed one page at a time
- Erased one block at a time
$\square$ Example:
- 4096-bit pages

- 16 pages / 8 KB block
- Many blocks / memory


## 64 Gb NAND Flash

$\square 64 \mathrm{~K}$ cells / page
$\square 4$ bits / cell (multiple $V_{t}$ )

- 64 cells / string
- 256 pages / block
$\square$ 2K blocks / plane
- 2 planes

[Trinh09]


## Building Logic with ROMs

$\square$ Use ROM as lookup table containing truth table
-n inputs, k outputs requires words x bits

- Changing function is easy - reprogram ROM
$\square$ Finite State Machine
- n inputs, k outputs, s bits of state
- Build with
inputs

k outputs
bit ROM and bit reg



## Example: RoboAnt

## Let's build an Ant

Sensors: Antennae
(L,R) - 1 when in contact
Actuators: Legs
Forward step F
Ten degree turns TL, TR

Goal: make our ant smart enough to get out of a maze

Strategy: keep right antenna on wall

(RoboAnt adapted from MIT 6.0042002 OpenCourseWare by Ward and Terman)

## Lost in space


$\square$ Action: go forward until we hit something

- Initial state



## Bonk!!!



A Action: turn left (rotate counterclockwise)

- Until we don't touch anymore



## A little to the right


$\square$ Action: step forward and turn right a little

- Looking for wall



## Then a little to the left


$\square$ Action: step and turn left a little, until not touching


## Whoops - a corner!


$\square$ Action: step and turn right until hitting next wall


## Simplification

## $\square$ Merge equivalent states where possible



## State Transition Table



## ROM Implementation

- 16-word $\times 5$ bit ROM



## ROM Implementation

- 16-word $\times 5$ bit ROM



## PLAs

- A Programmable Logic Array performs any function in sum-of-products form.
$\square$ Literals: inputs \& complements
- Products / Minterms: AND of literals
- Outputs: OR of Minterms
- Example: Full Adder
$s=a \bar{b} \bar{c}+\bar{a} b \bar{c}+\bar{a} \bar{b} c+a b c$
$c_{\text {out }}=a b+b c+a c$



## NOR-NOR PLAs

$\square$ ANDs and ORs are not very efficient in CMOS
$\square$ Dynamic or Pseudo-nMOS NORs are very efficient
$\square$ Use DeMorgan's Law to convert to all NORs


## PLA Schematic \& Layout



## PLAs vs. ROMs

$\square$ The OR plane of the PLA is like the ROM array
$\square$ The AND plane of the PLA is like the ROM decoder
$\square$ PLAs are more flexible than ROMs

- No need to have $2^{n}$ rows for $n$ inputs
- Only generate the minterms that are needed
- Take advantage of logic simplification


## Example: RoboAnt PLA

$\square$ Convert state transition table to logic equations

| $\mathrm{S}_{1: 0}$ | L | R | $\mathrm{S}_{1: 0}$ | TR | TL | F |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| 00 | 0 | 0 | 00 | 0 | 0 | 1 |
| 00 | 1 | X | 01 | 0 | 0 | 1 |
| 00 | 0 | 1 | 01 | 0 | 0 | 1 |
| 01 | 1 | X | 01 | 0 | 1 | 0 |
| 01 | 0 | 1 | 01 | 0 | 1 | 0 |
| 01 | 0 | 0 | 10 | 0 | 1 | 0 |
| 10 | X | 0 | 10 | 1 | 0 | 1 |
| 10 | X | 1 | 11 | 1 | 0 | 1 |
| 11 | 1 | X | 01 | 0 | 1 | 1 |
| 11 | 0 | 0 | 10 | 0 | 1 | 1 |
| 11 | 0 | 1 | 11 | 0 | 1 | 1 |

$$
\begin{aligned}
& \begin{array}{rrrrrr} 
& & & \\
& & & & \\
& 00 & 01 & 11 & 10 \\
\text { LR } & 0 & 0 & 1 & 1 & 1 \\
11 & 0 & 0 & 0 & 1 & 1 \\
10 & 0 & 0 & 0 & 1 \\
& 0 & 1
\end{array} \\
& S_{1}^{\prime}=S_{1} \overline{S_{0}}+\bar{L} S_{1}+\overline{L R} S_{0} \\
& \\
& S_{0}^{\prime}=R+L \bar{S}_{1}+L S_{0} \\
& T R=S_{1} \bar{S}_{0} \\
& T L=S_{0} \\
& F=S_{1}+\bar{S}_{0}
\end{aligned}
$$

## RoboAnt Dot Diagram

$$
\begin{aligned}
S 1^{\prime} & =S_{1} \overline{S_{0}}+\bar{L} S_{1}+\bar{L} \bar{R} S_{0} \\
S 0^{\prime} & =R+L \overline{S_{1}}+L S_{0} \\
T R & =S_{1} \overline{S_{0}} \\
T L & =S_{0} \\
F & =S_{1}+\overline{S_{0}}
\end{aligned}
$$



